

*Advance Information*

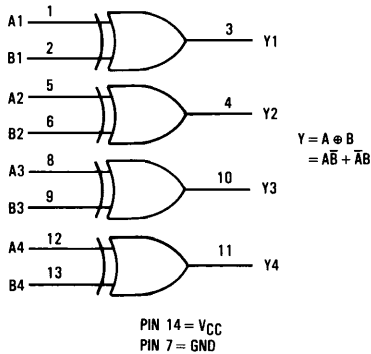
**Quad 2-Input Exclusive OR Gate**  
**High-Performance Silicon-Gate CMOS**

The MC54/74HC386 is identical in pinout to the LS386. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

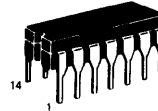
The HC386 is identical in function to the HC86, but has a different pin assignment.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 56 FETs or 14 Equivalent Gates

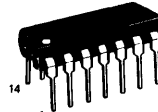
**LOGIC DIAGRAM**



**MC54/74HC386**



**J SUFFIX**  
**CERAMIC**  
**CASE 632-08**



**N SUFFIX**  
**PLASTIC**  
**CASE 646-06**



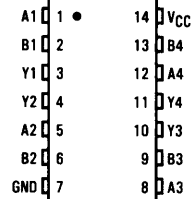
**D SUFFIX**  
**SOIC**  
**CASE 751A-02**

**ORDERING INFORMATION**

MC74HCXXXN	Plastic
MC54HCXXXJ	Ceramic
MC74HCXXXD	SOIC

$T_A = -55^\circ$  to  $125^\circ\text{C}$  for all packages.  
 Dimensions in Chapter 6.

**PIN ASSIGNMENT**



**FUNCTION TABLE**

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

**5**

This document contains information on a new product. Specifications and information herein are subject to change without notice.

# MC54/74HC386

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-1.5 to V <sub>CC</sub> +1.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: -10 mW/°C from 65° to 125°C

Ceramic DIP: -10 mW/°C from 100° to 125°C

SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> =2.0 V V <sub>CC</sub> =4.5 V V <sub>CC</sub> =6.0 V	0 0 0	1000 500 400
				ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				25°C to -55°C	≤85°C	≤125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND  I <sub>out</sub>   ≤ 4.0 mA  I <sub>out</sub>   ≤ 5.2 mA	2.0	0.26	0.33	0.40	μA
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	6.0	±0.1	±1.0	±1.0	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

# MC54/74HC386

## AC ELECTRICAL CHARACTERISTICS (C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6 ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			25°C to -55°C	≤ 85°C	≤ 125°C	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 4.5 6.0	120 24 20	150 30 26	180 36 31	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	—	10	10	10	pF

### NOTES:

1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

C <sub>PD</sub>	Power Dissipation Capacitance (Per Gate) Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V <sub>CC</sub> = 5.0 V	pF
		33	

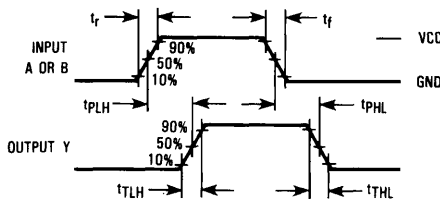
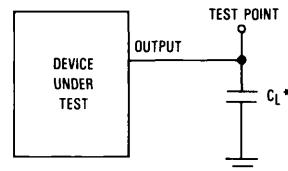


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance.

Figure 2. Test Circuit

5

## EXPANDED LOGIC DIAGRAM (% of the Device Shown)

